



仁懋电子

MOT3180G
N-CHANNEL MOSFET

■ PRODUCT CHARACTERISTICS

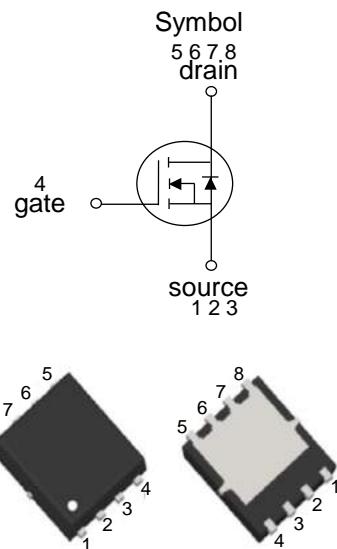
V _{DSS}	30V
R _{D(on)} Typ(@V _{GS} =10V)	5.5mΩ
R _{D(on)} Typ(@V _{GS} =4.5V)	9mΩ
I _D	40A

■ APPLICATIONS

DC/DC converter
Ideal for high-frequency switching
and synchronous rectification

■ FEATURES

Very low on-resistance R_{D(on)}
Good stability and uniformity with high E_{AS}
Pb-free lead plating



PDFN5X6-8L

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT3180G	PDFN5X6-8L	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_C=25°C,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	±20	V
Drain current	I _D	40	A
	I _D	28.3	A
Pulsed drain current	I _{DM}	160	A
Avalanche energy single pulsed	E _{AS}	150	mJ
Power dissipation	P _D	35	W
Junction temperature	T _J	+150	°C
Storage temperature	T _{STG}	-55~+150	°C

■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{DS}}=250\mu\text{A}$	30	-	-	V
Drain-source leakage current	I_{DSS}	$\text{V}_{\text{DS}}=30\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-source leakage current	I_{GSS}	$\text{V}_{\text{GS}}=\pm20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	100	nA
On characteristics						
Gate threshold voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{DS}}=250\mu\text{A}$	1	-	2.5	V
On-state characteristics	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_{\text{D}}=20\text{A}$	-	5.5	8	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_{\text{D}}=20\text{A}$	-	9	13	$\text{m}\Omega$
Forward transconductance	g_{FS}	$\text{V}_{\text{DS}}=10\text{V}, \text{I}_{\text{D}}=20\text{A}$	10	-	-	S
Dynamic characteristics						
Input capacitance	C_{iss}	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=15\text{V}$ $f=1\text{MHz}$	-	1650	-	pF
Out capacitance	C_{oss}		-	205	-	pF
Reverse transfer capacitance	C_{rss}		-	177	-	pF
Switching characteristics						
Total gate charge	Q_g	$\text{V}_{\text{GS}}=10\text{V}, \text{V}_{\text{DS}}=15\text{V}$ $\text{I}_{\text{D}}=20\text{A}$	-	32.3	-	nC
Gate-source charge	Q_{gs}		-	4.9	-	nC
Gate-drain charge	Q_{gd}		-	6.9	-	nC
Turn-on delay time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{DD}}=15\text{V}, \text{I}_{\text{D}}=20\text{A}$ $\text{R}_{\text{G}}=6\Omega, \text{V}_{\text{GS}}=10\text{V}$	-	9	-	nS
Turn-on rise time	t_r		-	8	-	nS
Turn-off delay time	$\text{t}_{\text{d(off)}}$		-	28	-	nS
Turn-off fall time	t_f		-	5	-	nS
Source-drain diode ratings and characteristics						
Continuous diode forward current	I_{SD}		-	-	40	A
Diode forward current	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{SD}}=20\text{A}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$\text{I}_{\text{F}}=20\text{A}$ $d\text{I}/dt=100\text{A}/\mu\text{s}$	-	27	-	nS
Reverse recovery charge	Q_{rr}		-	20	-	nC

■ TYPICAL CHARACTERISTICS

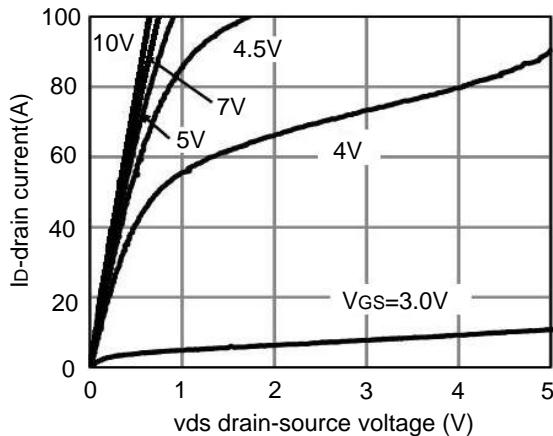


Fig.1 output characteristics

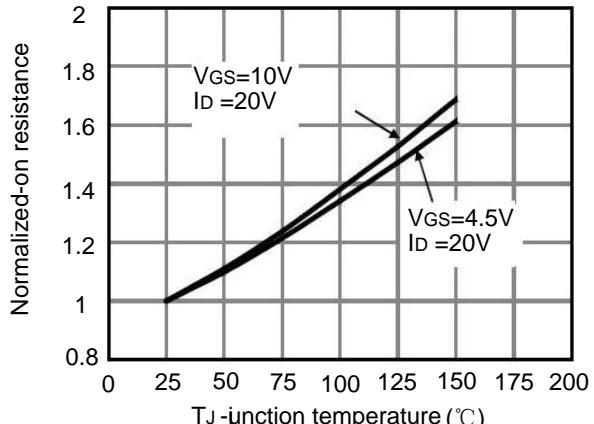


Fig.2 rdson-junction temperature

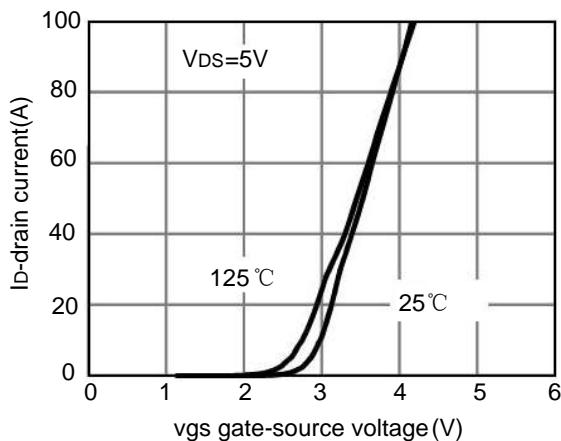


Fig.3 transfer characteristics

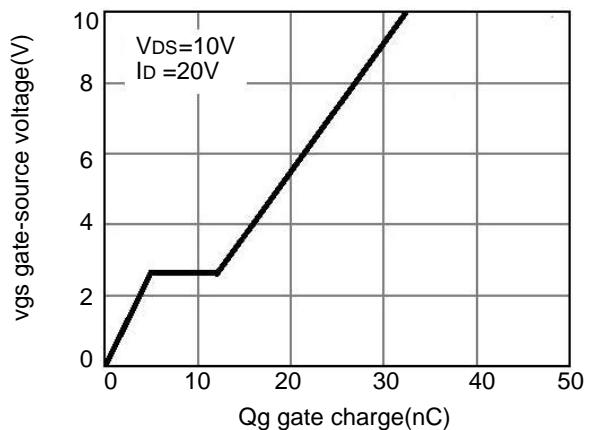


Fig.4 gare charge]

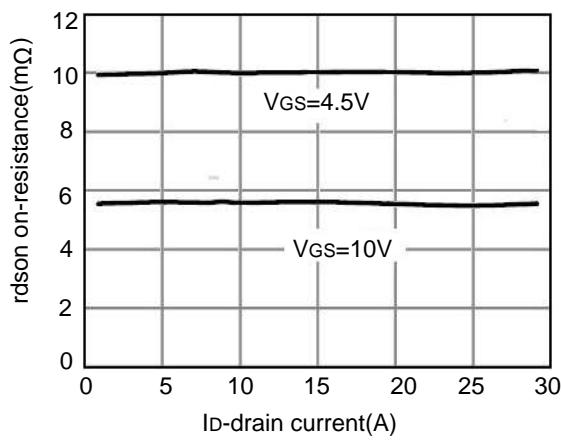


Fig.5 rdson-drain current

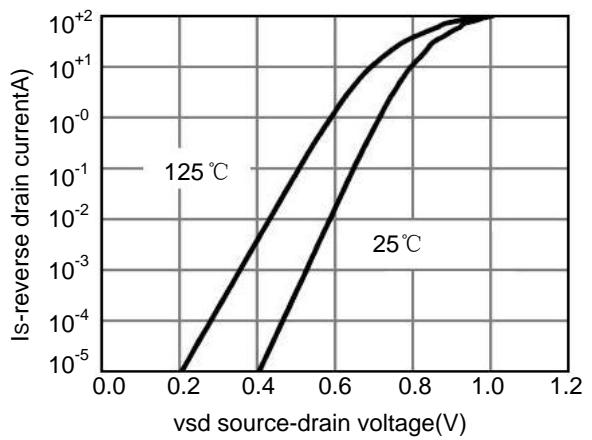


Fig.6 source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

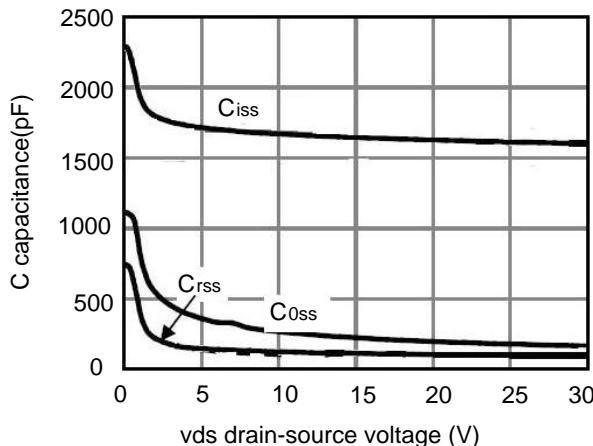


Fig.7 capacitance vs vds

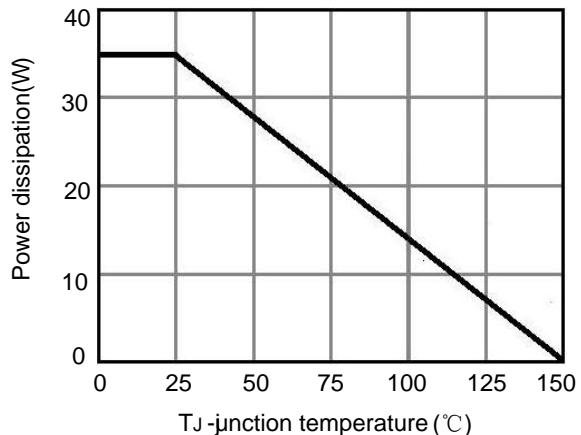


Fig.8 power de-rating

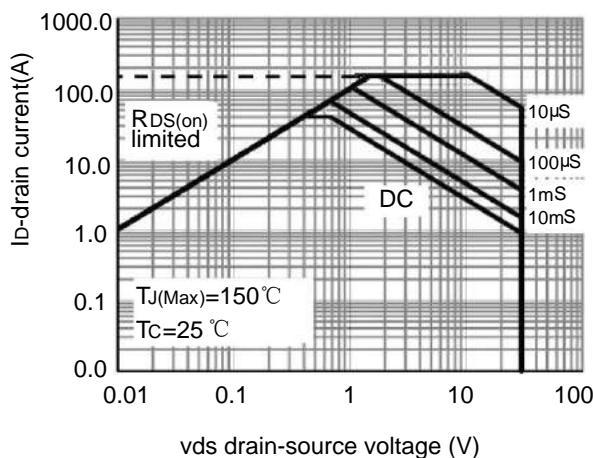


Fig.9 safe operation area

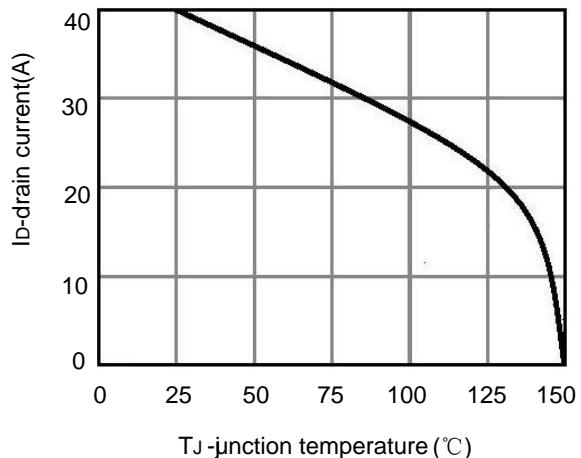
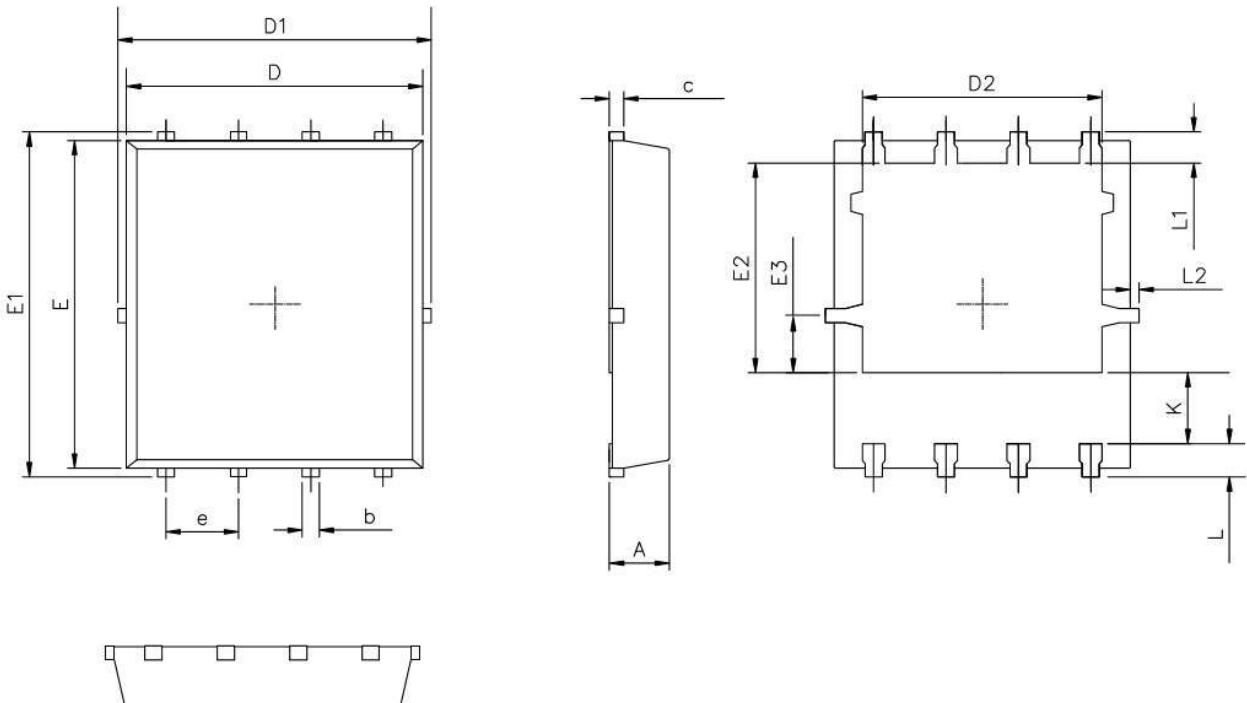
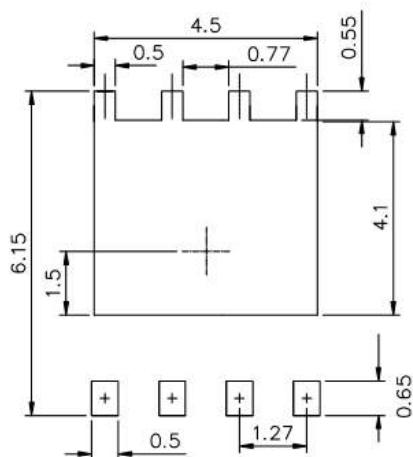


Fig.10 id current-junction temperature

■ PDFN5X6-8L PACKAGE MECHANICAL DATA



RECOMMENDED LAND PATTERN



	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50